

**32K x 16 Static RAM**

**Features**

- High speed
  - $t_{AA} = 12, 15 \text{ ns}$
- CMOS for optimum speed/power
- Low active power
  - 825 mW (max.)
- Low CMOS standby power (L version only)
  - 2.75 mW (max.)
- Automatic power-down when deselected
- Independent control of upper and lower bits
- Available in 44-pin TSOP II and 400-mil SOJ

**Functional Description**

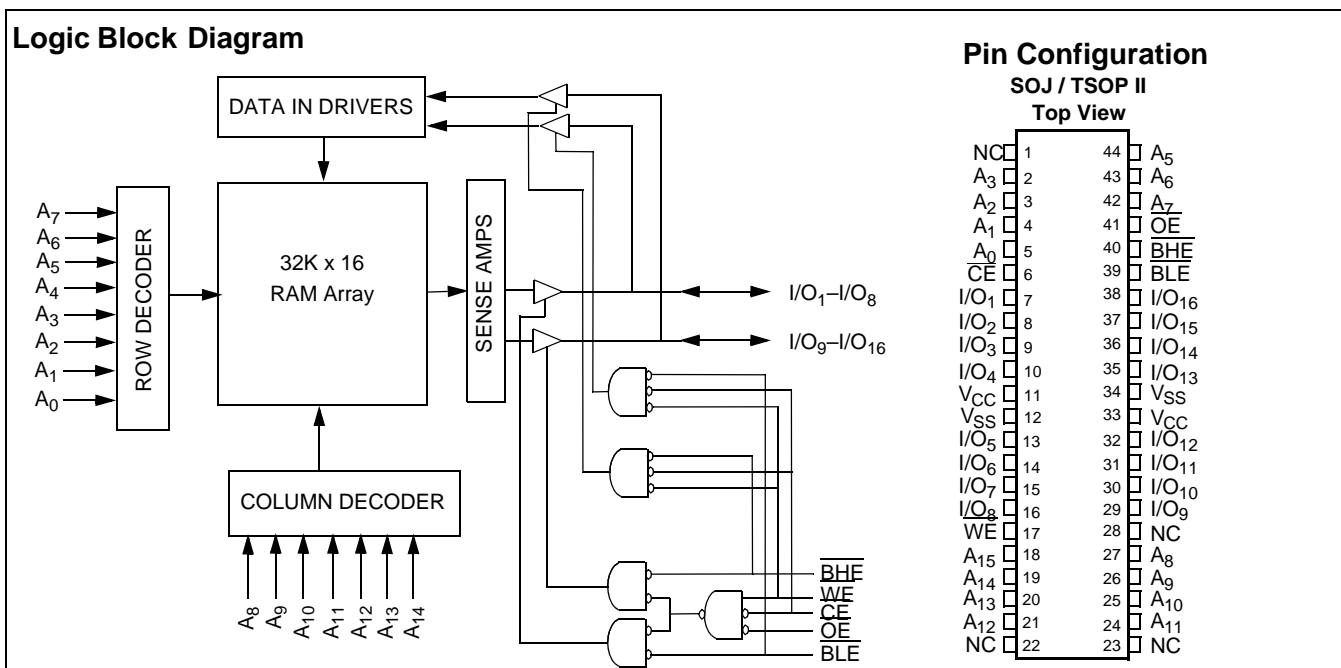
The CY7C1020BN is a high-performance CMOS static RAM organized as 32,768 words by 16 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from I/O pins ( $I/O_1$  through  $I/O_8$ ), is written into the location specified on the address pins ( $A_0$  through  $A_{15}$ ). If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from I/O pins ( $I/O_9$  through  $I/O_{16}$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{15}$ ).

Reading from the device is accomplished by taking Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing the Write Enable ( $\overline{WE}$ ) HIGH. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from the memory location specified by the address pins will appear on  $I/O_1$  to  $I/O_8$ . If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from memory will appear on  $I/O_9$  to  $I/O_{16}$ . See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins ( $I/O_1$  through  $I/O_{16}$ ) are placed in a high-impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), the  $\overline{BHE}$  and  $\overline{BLE}$  are disabled ( $\overline{BHE}$ ,  $\overline{BLE}$  HIGH), or during a write operation ( $\overline{CE}$  LOW, and  $\overline{WE}$  LOW).

The CY7C1020BN is available in standard 44-pin TSOP Type II and 400-mil-wide SOJ packages.



**Selection Guide**

		7C1020BN-12	7C1020BN-15
Maximum Access Time (ns)		12	15
Maximum Operating Current (mA)		140	130
Maximum CMOS Standby Current (mA)		3	3
	L	0.5	0.5

**Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... -65°C to +150°C

Ambient Temperature with Power Applied ..... -55°C to +125°C

Supply Voltage on V<sub>CC</sub> to Relative GND<sup>[1]</sup> .... -0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State<sup>[1]</sup> ..... -0.5V to V<sub>CC</sub>+0.5V

DC Input Voltage<sup>[1]</sup> ..... -0.5V to V<sub>CC</sub>+0.5V

Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

**Operating Range**

Range	Ambient Temperature <sup>[2]</sup>	V <sub>CC</sub>
Commercial	0°C to +70°C	5V ± 10%
Industrial	-40°C to +85°C	5V ± 10%

**Electrical Characteristics** Over the Operating Range

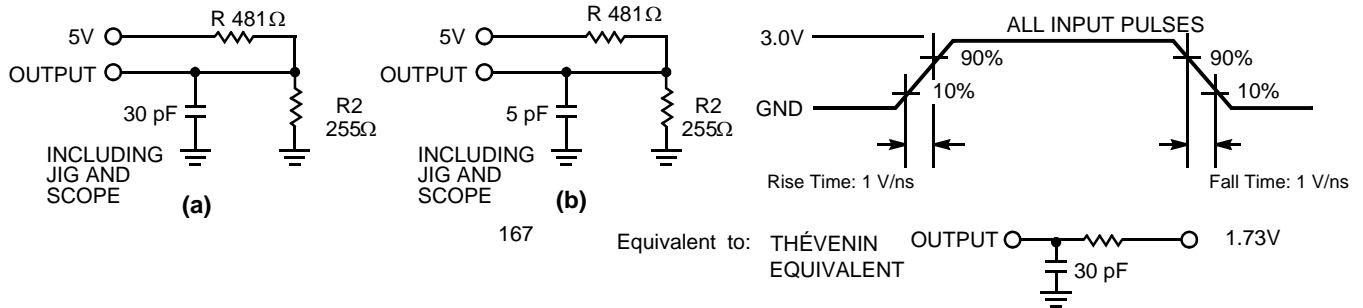
Parameter	Description	Test Conditions	7C1020BN-12		7C1020BN-15		Unit
			Min.	Max.	Min.	Max.	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = -4.0 mA	2.4		2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA		0.4		0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	6.0	2.2	6.0	V
V <sub>IL</sub>	Input LOW Voltage <sup>[1]</sup>		-0.5	0.8	-0.5	0.8	V
I <sub>Ix</sub>	Input Load Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>	-1	+1	-1	+1	μA
I <sub>OZ</sub>	Output Leakage Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub> , Output Disabled	-1	+1	-1	+1	μA
I <sub>OS</sub>	Output Short Circuit Current <sup>[3]</sup>	V <sub>CC</sub> = Max., V <sub>OUT</sub> = GND		-300		-300	mA
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max., I <sub>OUT</sub> = 0 mA, f = f <sub>MAX</sub> = 1/t <sub>RC</sub>		140		130	mA
I <sub>SB1</sub>	Automatic CE Power-Down Current—TTL Inputs	Max. V <sub>CC</sub> , $\overline{CE} \geq V_{IH}$ V <sub>IN</sub> ≥ V <sub>IH</sub> or V <sub>IN</sub> ≤ V <sub>IL</sub> , f = f <sub>MAX</sub>		20		20	mA
I <sub>SB2</sub>	Automatic CE Power-Down Current—CMOS Inputs	Max. V <sub>CC</sub> , $\overline{CE} \geq V_{CC} - 0.3V$ , V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.3V, or V <sub>IN</sub> ≤ 0.3V, f = 0		3		3	mA
		L		0.5		0.5	mA

**Capacitance<sup>[4]</sup>**

Parameter	Description	Test Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	T <sub>A</sub> = 25°C, f = 1 MHz, V <sub>CC</sub> = 5.0V	8	pF
C <sub>OUT</sub>	Output Capacitance		8	pF

**Notes:**

- V<sub>IL</sub> (min.) = -2.0V for pulse durations of less than 20 ns.
- T<sub>A</sub> is the case temperature.
- Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
- Tested initially and after any design or process changes that may affect these parameters.

**AC Test Loads and Waveforms**

**Switching Characteristics<sup>[5]</sup> Over the Operating Range**

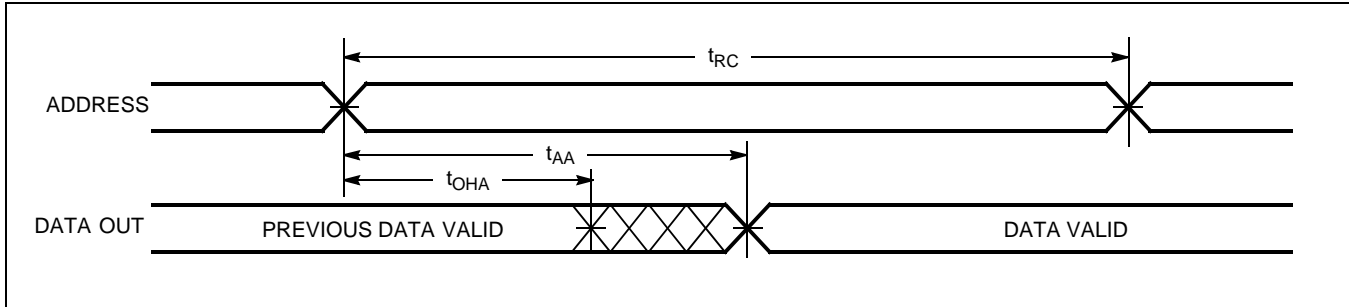
Parameter	Description	7C1020BN-12		7C1020BN-15		Unit
		Min.	Max.	Min.	Max.	
<b>Read Cycle</b>						
$t_{RC}$	Read Cycle Time	12		15		ns
$t_{AA}$	Address to Data Valid		12		15	ns
$t_{OHA}$	Data Hold from Address Change	3		3		ns
$t_{ACE}$	$\overline{CE}$ LOW to Data Valid		12		15	ns
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid		6		7	ns
$t_{LZOE}$	$\overline{OE}$ LOW to Low Z <sup>[6]</sup>	0		0		ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z <sup>[6, 7]</sup>		6		7	ns
$t_{LZCE}$	$\overline{CE}$ LOW to Low Z <sup>[6]</sup>	3		3		ns
$t_{HZCE}$	$\overline{CE}$ HIGH to High Z <sup>[6, 7]</sup>		6		7	ns
$t_{PU}$	$\overline{CE}$ LOW to Power-Up	0		0		ns
$t_{PD}$	$\overline{CE}$ HIGH to Power-Down		12		15	ns
$t_{DBE}$	Byte Enable to Data Valid		6		7	ns
$t_{LZBE}$	Byte Enable to Low Z	0		0		ns
$t_{HZBE}$	Byte Disable to High Z		6		7	ns
<b>Write Cycle<sup>[8]</sup></b>						
$t_{WC}$	Write Cycle Time	12		15		ns
$t_{SCE}$	$\overline{CE}$ LOW to Write End	9		10		ns
$t_{AW}$	Address Set-Up to Write End	8		10		ns
$t_{HA}$	Address Hold from Write End	0		0		ns
$t_{SA}$	Address Set-Up to Write Start	0		0		ns
$t_{PWE}$	$\overline{WE}$ Pulse Width	8		10		ns
$t_{SD}$	Data Set-Up to Write End	6		8		ns
$t_{HD}$	Data Hold from Write End	0		0		ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low Z <sup>[6]</sup>	3		3		ns
$t_{HZWE}$	$\overline{WE}$ LOW to High Z <sup>[6, 7]</sup>		6		7	ns
$t_{BW}$	Byte Enable to End of Write	8		9		ns

**Notes:**

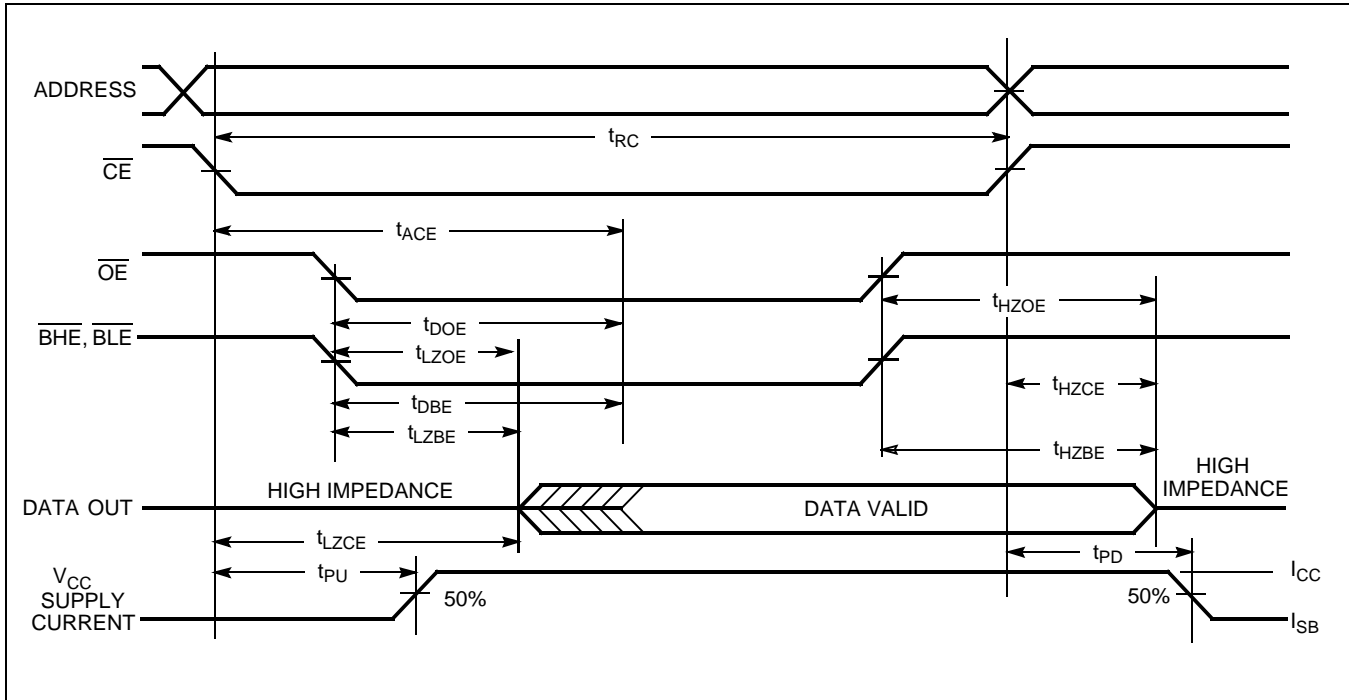
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified  $I_{OL}/I_{OH}$  and 30-pF load capacitance.
- At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
- $t_{HZOE}$ ,  $t_{HZBE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured  $\pm 500$  mV from steady-state voltage.
- The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW,  $\overline{WE}$  LOW and  $\overline{BHE}$  /  $\overline{BLE}$  LOW.  $\overline{CE}$ ,  $\overline{WE}$  and  $\overline{BHE}$  /  $\overline{BLE}$  must be LOW to initiate a write, and the transition of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.

### Switching Waveforms

Read Cycle No. 1<sup>[9, 10]</sup>



Read Cycle No. 2 (OE Controlled)<sup>[10, 11]</sup>

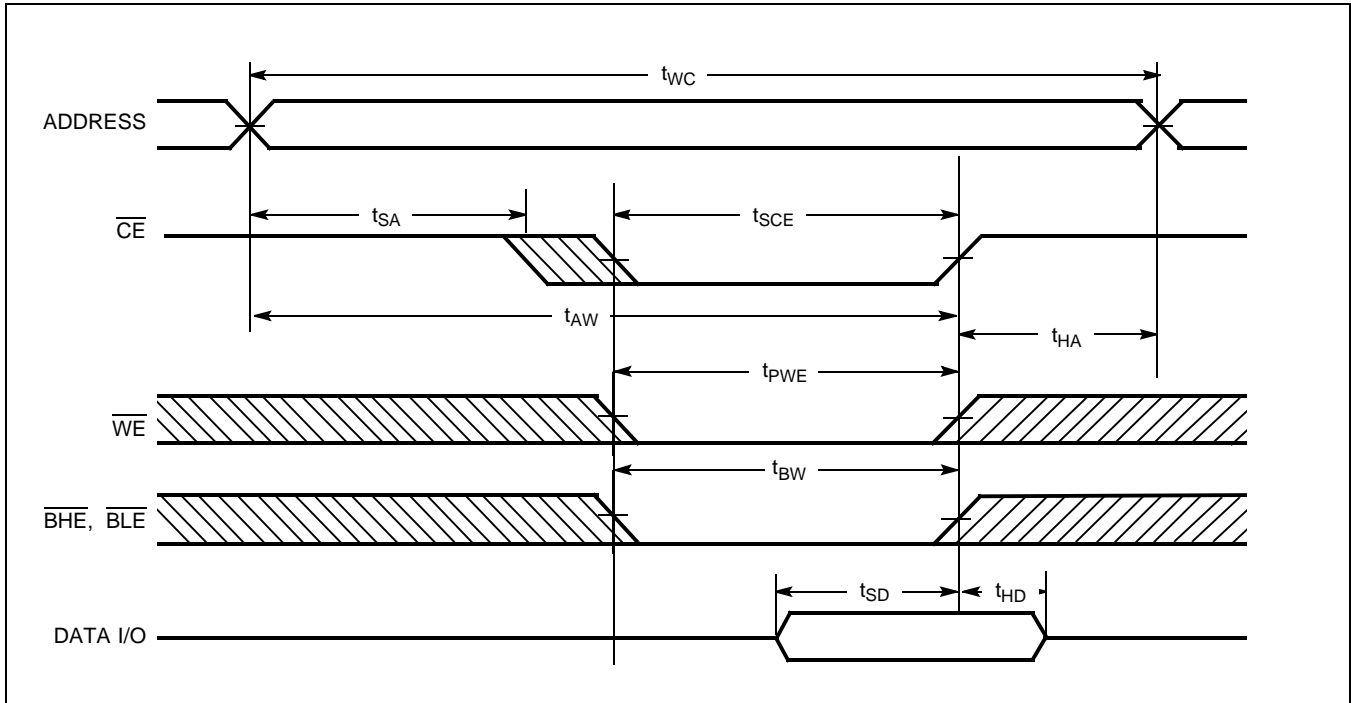


**Notes:**

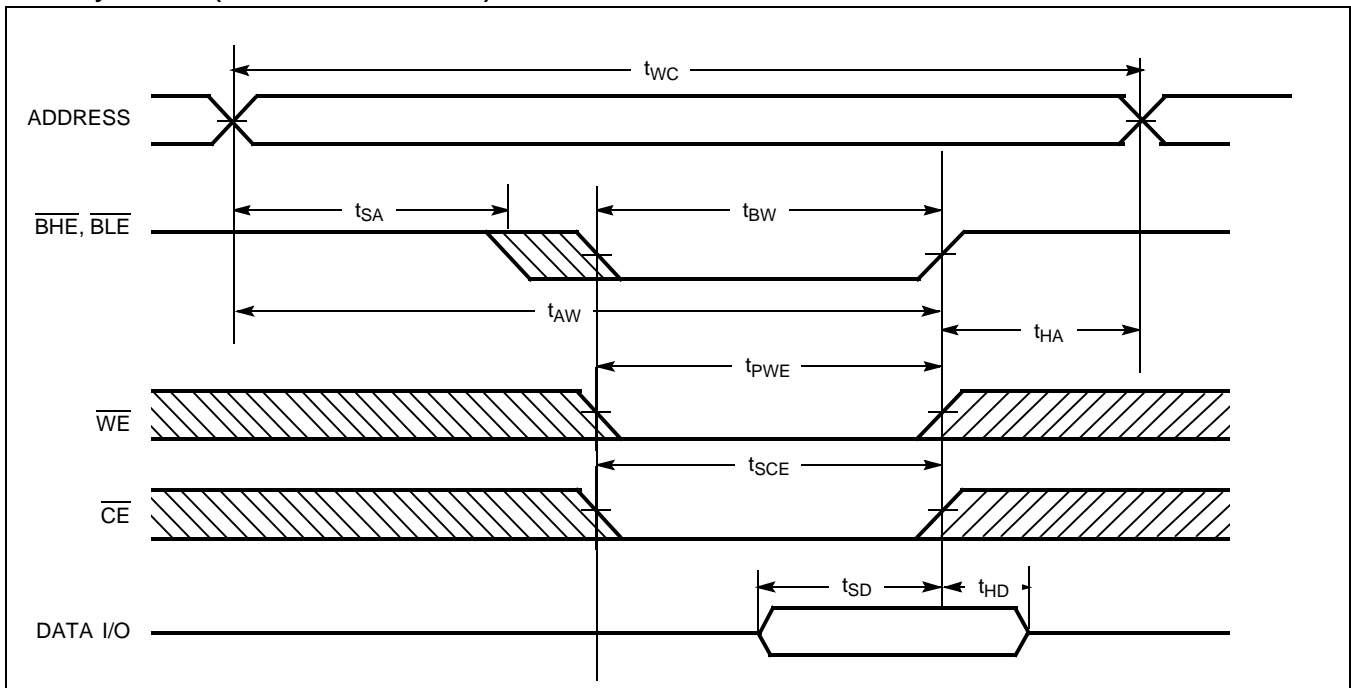
- 9. Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{BHE}$  and/or  $\overline{BLE}$  =  $V_{IL}$ .
- 10.  $\overline{WE}$  is HIGH for read cycle.
- 11. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ( $\overline{\text{CE}}$  Controlled)<sup>[12, 13]</sup>



Write Cycle No. 2 (BLE or BHE Controlled)

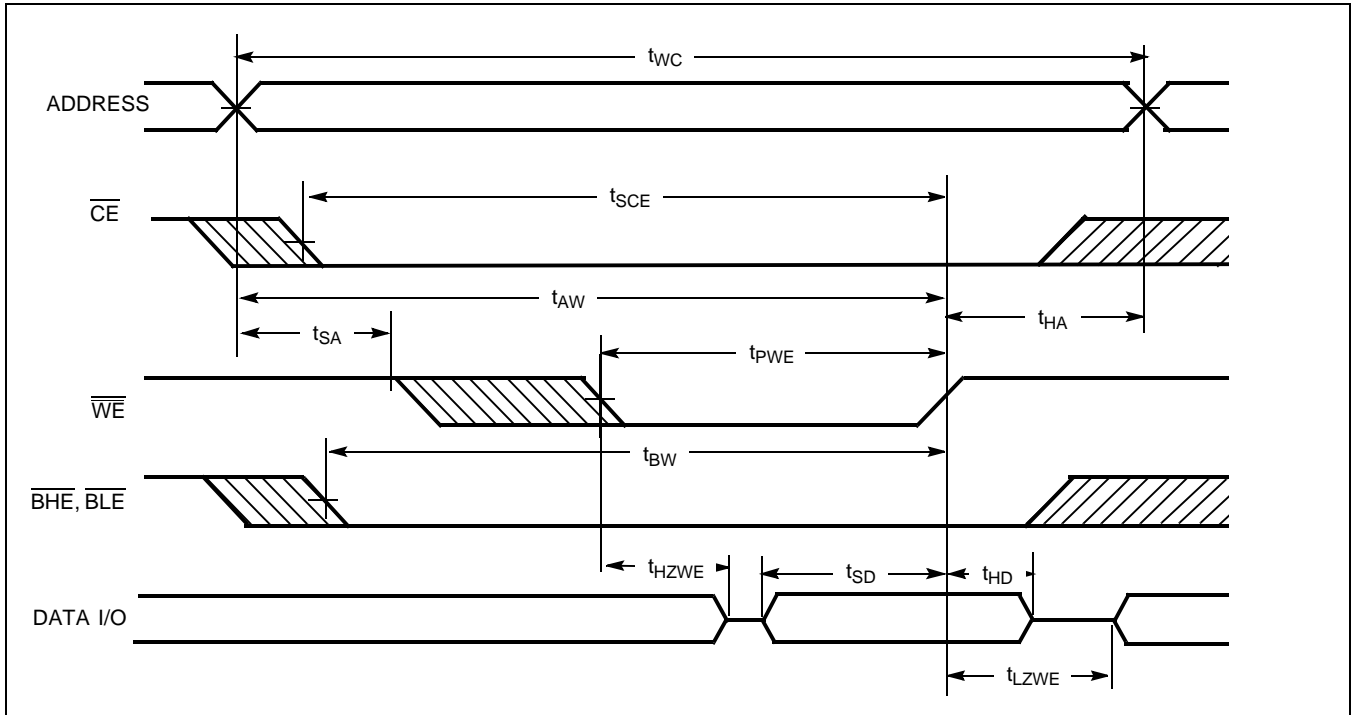


Notes:

- 12. Data I/O is high impedance if  $\overline{\text{OE}}$  or  $\overline{\text{BHE}}$  and/or  $\overline{\text{BLE}} = V_{IH}$ .
- 13. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high-impedance state.

**Switching Waveforms** (continued)

**Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW)**



**Truth Table**

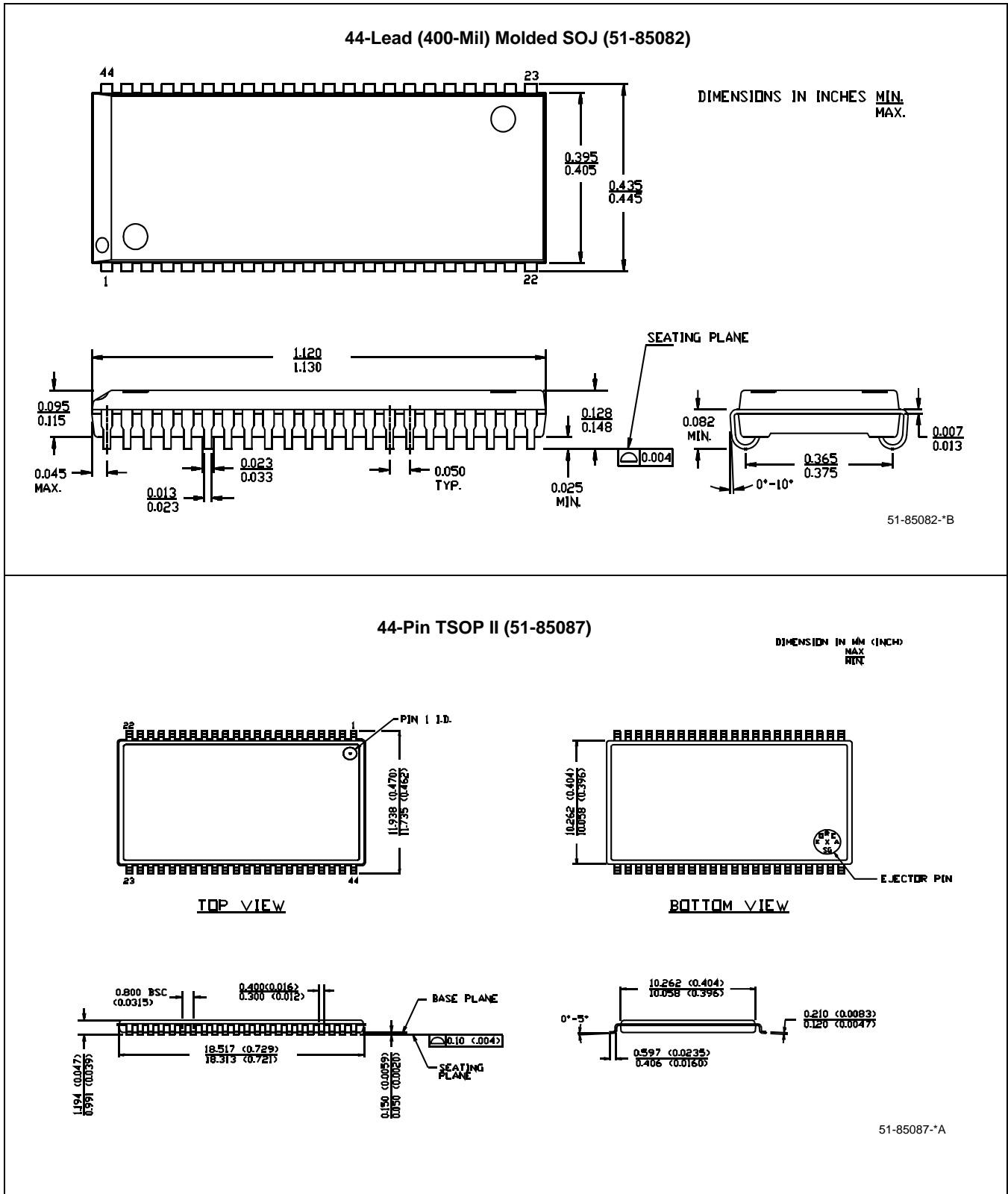
$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O <sub>1</sub> -I/O <sub>8</sub>	I/O <sub>9</sub> -I/O <sub>16</sub>	Mode	Power
H	X	X	X	X	High Z	High Z	Power-Down	Standby ( $I_{SB}$ )
L	L	H	L	L	Data Out	Data Out	Read – All bits	Active ( $I_{CC}$ )
			L	H	Data Out	High Z	Read – Lower bits only	Active ( $I_{CC}$ )
			H	L	High Z	Data Out	Read – Upper bits only	Active ( $I_{CC}$ )
L	X	L	L	L	Data In	Data In	Write – All bits	Active ( $I_{CC}$ )
			L	H	Data In	High Z	Write – Lower bits only	Active ( $I_{CC}$ )
			H	L	High Z	Data In	Write – Upper bits only	Active ( $I_{CC}$ )
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active ( $I_{CC}$ )
L	X	X	H	H	High Z	High Z	Selected, Outputs Disabled	Active ( $I_{CC}$ )

**Ordering Information**

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
12	CY7C1020BN-12VC	51-85082	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020BN-12VXC	51-85082	44-Lead (400-Mil) Molded SOJ (Pb-free)	Commercial
	CY7C1020BN-12ZC	51-85087	44-pin TSOP Type II	Commercial
	CY7C1020BN-12ZXC	51-85087	44-pin TSOP Type II (Pb-free)	Commercial
15	CY7C1020BN-15ZC	51-85087	44-pin TSOP Type II	Commercial
	CY7C1020BN-15ZXC	51-85087	44-pin TSOP Type II (Pb-free)	Commercial

Please contact local sales representative regarding availability of these parts.

Package Diagrams



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**Document History Page**

<b>Document Title: CY7C1020BN 32K x 16 Static RAM</b> <b>Document #: 001-06443</b>				
<b>REV.</b>	<b>ECN NO.</b>	<b>Issue Date</b>	<b>Orig. of Change</b>	<b>Description of Change</b>
**	426812	See ECN	NXR	New Data Sheet